



DMN2300U

20V N-CHANNEL ENHANCEMENT MODE MOSFET IN SOT23

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D Max (Note 6)
20V	175mΩ @ V _{GS} = 4.5V	1.40A @ T _A = +25°C
	240mΩ @ V _{GS} = 2.5V	1.20A @ T _A = +25°C
	360mΩ @ V _{GS} = 1.8V	1.0A @ T _A = +25°C

Features and Benefits

- On Resistance <200mΩ
- Low Gate Threshold Voltage
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- **ESD Protected Gate**

Description and Applications

This MOSFET has been designed to minimize the on-state resistance (RDS(ON)) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Load Switch

Mechanical Data

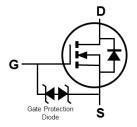
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208@3
- Weight: 0.08 grams (Approximate)

SOT23

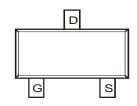








Equivalent Circuit



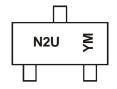
Top View

Ordering Information (Note 4)

	Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel	
	DMN2300U-7	N2U	7	8	3000	
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.						

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



N2U = Product Type Marking Code YM = Date Code Marking Y = Year (ex: G = 2019)M = Month (ex: 9 = September)

Date Code Key

Year	201	1	~		2019	20	20	2021		2022	2	2023
Code	Υ		~		G	ŀ	1			J		K
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Cha	racteristic		Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	20	V
Gate-Source Voltage			V _{GSS}	±8	V
Continuous Drain Current	Steady State	$T_A = +25$ °C (Note 6) $T_A = +85$ °C (Note 6) $T_A = +25$ °C (Note 5)	I _D	1.40 1.01 1.24	А
Pulsed Drain Current (Note 7)			I _{DM}	11	Α

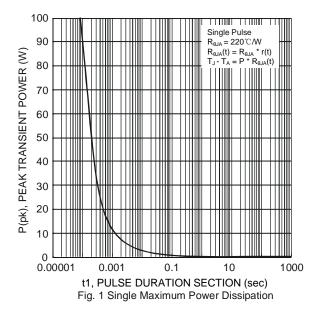
Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

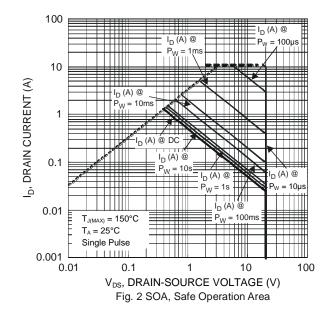
Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 5)	_	0.43	W
Power Dissipation	(Note 6)	P _D	0.55	W
Thermal Resistance, Junction to Ambient	(Note 5)	D	288	°C/W
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	228	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C	

Notes:

- 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
- 6. Device mounted on 25mm \times 25mm square copper plate with FR-4 substrate PC board, 2oz copper.
- 7. Device mounted on minimum recommended pad layout test board, 10µs pulse duty cycle = 1%.

Thermal Characteristics







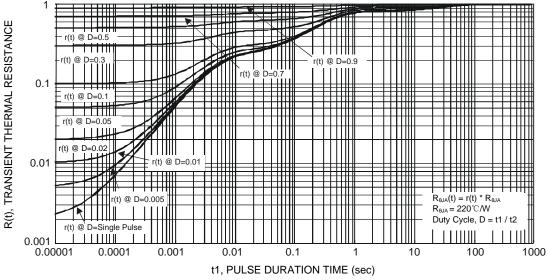


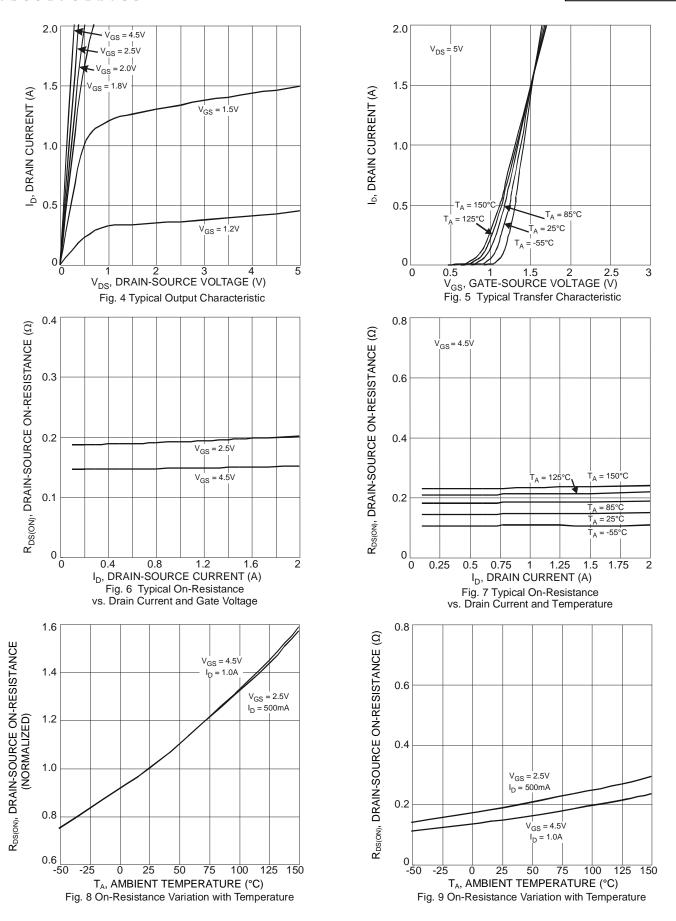
Fig. 3 Transient Thermal Resistance

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	20	_	_	V	$V_{GS} = 0V, I_D = 10\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	_	_	1	μΑ	V _{DS} = 20V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_	_	10	μΑ	$V_{GS} = \pm 8V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(TH)}	0.45	_	0.95	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
				175		$V_{GS} = 4.5V, I_D = 300mA$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	-	240	mΩ	$V_{GS} = 2.5V, I_D = 250mA$	
				360		$V_{GS} = 1.8V, I_D = 100mA$	
Forward Transfer Admittance	Y _{fs}	40	_	_	mS	$V_{DS} = 3V, I_{D} = 30mA$	
Diode Forward Voltage	V_{SD}	_	0.7	1.2	V	$V_{GS} = 0V, I_{S} = 300mA$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	_	67.6	_	pF	.,	
Output Capacitance	Coss	_	9.7	_	рF	$V_{DS} = 20V, V_{GS} = 0V,$ - f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	7.5	_	pF	1 = 1.000112	
Gate Resistance	R_{g}	_	70	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Qg	_	1.6	_	nC	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	
Gate-Source Charge	Qgs	_	0.2	_	nC	$V_{GS} = 4.5V, V_{DS} = 15V,$	
Gate-Drain Charge	Q_{gd}	_	0.2	_	nC	$I_D = 1A$	
Turn-On Delay Time	t _{D(ON)}	_	3.5	_	ns		
Turn-On Rise Time	t _R	_	2.8	_	ns	$V_{DS} = 10V, I_{D} = 1A$	
Turn-Off Delay Time	t _{D(OFF)}	_	38	_	ns	$V_{GS} = 10V, R_G = 6\Omega$	
Turn-Off Fall Time	t _F	_	13	_	ns	7	

Note: 8. Short duration pulse test used to minimize self-heating effect.







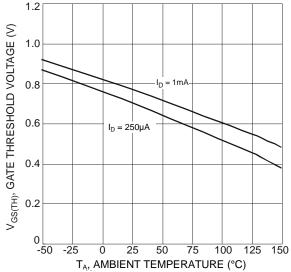
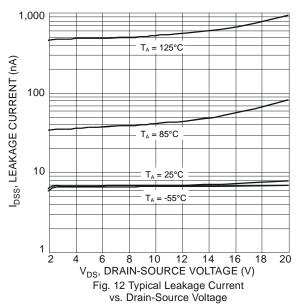
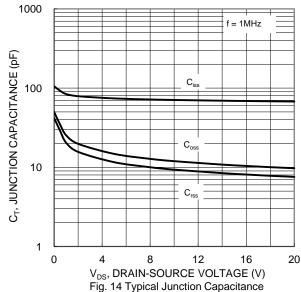
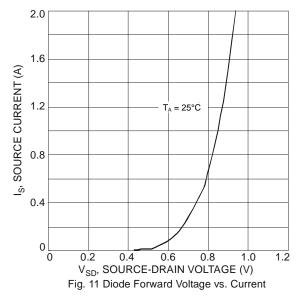
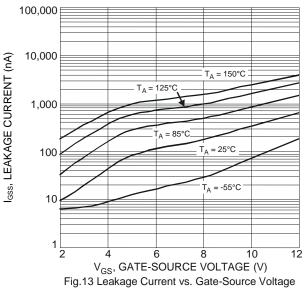


Fig. 10 Gate Threshold Variation vs. Ambient Temperature









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V_{DS} = 15V

V_{DS} = 15V

V_{DS} = 1A

V_{DS} = 15V

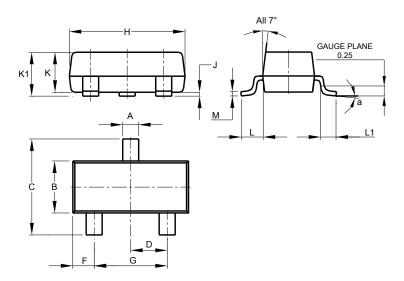
V_D



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

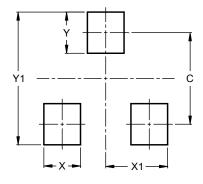


SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
7	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K 1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
а	a 0°						
All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Υ	0.9
Y1	2.9



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